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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	32MHz
Connectivity	I ² C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT, IBT LIN/J2602
Number of I/O	12
Program Memory Size	14KB (8K x 14)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.3V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	20-SSOP (0.209", 5.30mm Width)
Supplier Device Package	20-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16f1829lin-i-ss

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Peripheral Highlights (Continued)

- · Data Signal Modulator Module:
- Selectable modulator and carrier sources
- SR Latch:
- Multiple Set/Reset input options
- Emulates 555 Timer applications

ECCP (Full-Bridge) ECCP (Half-Bridge) MSSP (I²CTM/SPI) Sheet Index Program Memory 10-bit ADC (ch) Data EEPROM CapSense (ch) Flash (words) Comparators Data SRAM (8/16-bit) EUSART SR Latch Timers I/O's⁽²⁾ Debug⁽¹⁾ (bytes) (bytes) СC ХГР Device Data PIC12(L)F1822 (1) 2K 256 128 6 4 4 1 2/1 1 1 0/1/0 Y I/H Υ PIC12(L)F1840 4K 256 256 6 4 4 1 2/1 0/1/0 Y I/H Y (2)1 1 PIC16(L)F1823 (1) 2K 256 128 12 8 8 2 2/1 1 1 1/0/0 Y I/H Y PIC16(L)F1824 (3) 4K 256 256 12 8 8 2 4/1 1 1 1/1/2 Y I/H Υ PIC16(L)F1825 (4)8K 256 1024 12 8 8 2 4/1 1 1 1/1/2 Υ I/H Υ 12 2 1/0/0 I/H Υ PIC16(L)F1826 (5)2K 256 256 16 12 2/1 1 1 Υ PIC16(L)F1827 (5) 4K 256 384 16 12 12 2 4/1 1 2 1/1/2 Y I/H Y Y Y PIC16(L)F1828 (3)4K 256 256 18 12 12 2 4/1 1 1 1/1/2I/H PIC16(L)F1829 (4)8K 256 1024 18 12 12 2 4/1 1 2 1/1/2 Υ I/H Υ PIC16(L)F1847 8K 256 16 12 12 2 4/1 2 1/1/2 Y I/H Y (6)1024 1

PIC12(L)F1822/1840/PIC16(L)F182x/1847 Family Types

Note 1: I - Debugging, Integrated on Chip; H - Debugging, available using Debug Header.

2: One pin is input-only.

Data Sheet Index: (Unshaded devices are described in this document.)

1: DS41413 PIC12(L)F1822/PIC16(L)F1823 Data Sheet, 8/14-Pin Flash Microcontrollers.

2: DS41441 PIC12(L)F1840 Data Sheet, 8-Pin Flash Microcontrollers.

3: DS41419 PIC16(L)F1824/1828 Data Sheet, 28/40/44-Pin Flash Microcontrollers.

4: DS41440 PIC16(L)F1825/1829 Data Sheet, 14/20-Pin Flash Microcontrollers.

5: DS41391 PIC16(L)F1826/1827 Data Sheet, 18/20/28-Pin Flash Microcontrollers.

6: DS41453 PIC16(L)F1847 Data Sheet, 18/20/28-Pin Flash Microcontrollers.

Note: For other small form-factor package availability and marking information, please visit www.microchip.com/packaging or contact your local sales office.

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Errata

An errata sheet, describing minor operational differences from the data sheet and recommended workarounds, may exist for current devices. As device/documentation issues become known to us, we will publish an errata sheet. The errata will specify the revision of silicon and revision of document to which it applies.

To determine if an errata sheet exists for a particular device, please check with one of the following:

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3.1.1.2 Indirect Read with FSR

The program memory can be accessed as data by setting bit 7 of the FSRxH register and reading the matching INDFx register. The MOVIW instruction will place the lower eight bits of the addressed word in the W register. Writes to the program memory cannot be performed via the INDF registers. Instructions that access the program memory via the FSR require one extra instruction cycle to complete. Example 3-2 demonstrates accessing the program memory via an FSR.

The High directive will set bit<7> if a label points to a location in program memory.

EXAMPLE 3-2: ACCESSING PROGRAM MEMORY VIA FSR

constants			
RETLW	DATA0	;Index0	data
RETLW	DATA1	;Index1	data
RETLW	DATA2		
RETLW	DATA3		
my_functi	on		
; LO	IS OF CODE.		
MOVLW	LOW cons	tants	
MOVWF	FSR1L		
MOVLW	HIGH con	stants	
MOVWF	FSR1H		
MOVIW	0[FSR1]		
;THE PROG	RAM MEMORY	IS IN W	

3.2 Data Memory Organization

The data memory is partitioned in 32 memory banks with 128 bytes in a bank. Each bank consists of (Figure 3-2):

- · 12 core registers
- 20 Special Function Registers (SFR)
- Up to 80 bytes of General Purpose RAM (GPR)
- 16 bytes of common RAM

The active bank is selected by writing the bank number into the Bank Select Register (BSR). Unimplemented memory will read as '0'. All data memory can be accessed either directly (via instructions that use the file registers) or indirectly via the two File Select Registers (FSR). See **Section 3.5** "Indirect Addressing" for more information.

Data Memory uses a 12-bit address. The upper seven bits of the address define the Bank address and the lower five bits select the registers/RAM in that bank.

3.2.1 CORE REGISTERS

The core registers contain the registers that directly affect the basic operation of the PIC16(L)F1825/9. These registers are listed below:

- INDF0
- INDF1
- PCL
- STATUS
- FSR0 Low
- FSR0 High
- FSR1 Low
- FSR1 High
- BSR
- WREG
- PCLATH
- INTCON

Note: The core registers are the first 12 addresses of every data memory bank.

3.3 PCL and PCLATH

The Program Counter (PC) is 15 bits wide. The low byte comes from the PCL register, which is a readable and writable register. The high byte (PC<14:8>) is not directly readable or writable and comes from PCLATH. On any Reset, the PC is cleared. Figure 3-3 shows the five situations for the loading of the PC.

FIGURE 3-3: LOADING OF PC IN DIFFERENT SITUATIONS



3.3.1 MODIFYING PCL

Executing any instruction with the PCL register as the destination simultaneously causes the Program Counter PC<14:8> bits (PCH) to be replaced by the contents of the PCLATH register. This allows the entire contents of the program counter to be changed by writing the desired upper seven bits to the PCLATH register. When the lower eight bits are written to the PCL register, all 15 bits of the program counter will change to the values contained in the PCLATH register.

3.3.2 COMPUTED GOTO

A computed GOTO is accomplished by adding an offset to the program counter (ADDWF PCL). When performing a table read using a computed GOTO method, care should be exercised if the table location crosses a PCL memory boundary (each 256-byte block). Refer to the Application Note AN556, *"Implementing a Table Read"* (DS00556).

3.3.3 COMPUTED FUNCTION CALLS

A computed function CALL allows programs to maintain tables of functions and provide another way to execute state machines or look-up tables. When performing a table read using a computed function CALL, care should be exercised if the table location crosses a PCL memory boundary (each 256-byte block).

If using the CALL instruction, the PCH<2:0> and PCL registers are loaded with the operand of the CALL instruction. PCH<6:3> is loaded with PCLATH<6:3>.

The CALLW instruction enables computed calls by combining PCLATH and W to form the destination address. A computed CALLW is accomplished by loading the W register with the desired address and executing CALLW. The PCL register is loaded with the value of W and PCH is loaded with PCLATH.

3.3.4 BRANCHING

The branching instructions add an offset to the PC. This allows relocatable code and code that crosses page boundaries. There are two forms of branching, BRW and BRA. The PC will have incremented to fetch the next instruction in both cases. When using either branching instruction, a PCL memory boundary may be crossed.

If using BRW, load the W register with the desired unsigned address and execute BRW. The entire PC will be loaded with the address PC + 1 + W.

If using BRA, the entire PC will be loaded with PC + 1 +, the signed value of the operand of the BRA instruction.

3.4 Stack

All devices have a 16-level x 15-bit wide hardware stack (refer to Figures 3-4 through 3-7). The stack space is not part of either program or data space. The PC is PUSHed onto the stack when CALL or CALLW instructions are executed or an interrupt causes a branch. The stack is POPed in the event of a RETURN, RETLW or a RETFIE instruction execution. PCLATH is not affected by a PUSH or POP operation.

The stack operates as a circular buffer if the STVREN bit is programmed to '0' (Configuration Word 2). This means that after the stack has been PUSHed sixteen times, the seventeenth PUSH overwrites the value that was stored from the first PUSH. The eighteenth PUSH overwrites the second PUSH (and so on). The STKOVF and STKUNF flag bits will be set on an Overflow/Underflow, regardless of whether the Reset is enabled.

Note 1: There are no instructions/mnemonics called PUSH or POP. These are actions that occur from the execution of the CALL, CALLW, RETURN, RETLW and RETFIE instructions or the vectoring to an interrupt address.

3.4.1 ACCESSING THE STACK

The stack is available through the TOSH, TOSL and STKPTR registers. STKPTR is the current value of the Stack Pointer. TOSH:TOSL register pair points to the TOP of the stack. Both registers are read/writable. TOS is split into TOSH and TOSL due to the 15-bit size of the PC. To access the stack, adjust the value of STKPTR, which will position TOSH:TOSL, then read/write to TOSH:TOSL. STKPTR is five bits to allow detection of overflow and underflow.

Note:	Care should be taken when modifying the
	STKPTR while interrupts are enabled.

During normal program operation, CALL, CALLW and Interrupts will increment STKPTR while RETLW, RETURN, and RETFIE will decrement STKPTR. At any time STKPTR can be inspected to see how much stack is left. The STKPTR always points at the currently used place on the stack. Therefore, a CALL or CALLW will increment the STKPTR and then write the PC, and a return will unload the PC and then decrement the STKPTR.

Reference Figure 3-4 through Figure 3-7 for examples of accessing the stack.

FIGURE 3-4: ACCESSING THE STACK EXAMPLE 1

TOSH:TOSL 0x0F	STKPTR = 0x1F Stack Reset Disabled (STVREN = 0)
` 0х0Е	
0x0D	
0x0C	
0x0B	
0x0A	Initial Staals Configuration
0x09	
0x08	After Reset, the stack is empty. The empty stack is initialized so the Stack
0x07	Pointer is pointing at 0x1F. If the Stack Overflow/Underflow Reset is enabled, the
0x06	TOSH/TOSL registers will return '0'. If the Stack Overflow/Underflow Reset is
0x05	disabled, the TOSH/TOSL registers will return the contents of stack address 0x0E
0x04	
0x03	
0x02	
0x01	
0x00	
TOSH:TOSL 0x1F 0x0000	STKPTR = 0x1F Stack Reset Enabled (STVREN = 1)

REGISTER 4-1: CONFIGURATION WORD 1 (CONTINUED)

- bit 2-0 FOSC<2:0>: Oscillator Selection bits
 - 111 = ECH: External Clock, High-Power mode (4-32 MHz): device clock supplied to CLKIN pin
 - 110 = ECM: External Clock, Medium-Power mode (0.5-4 MHz): device clock supplied to CLKIN pin
 - 101 = ECL: External Clock, Low-Power mode (0-0.5 MHz): device clock supplied to CLKIN pin
 - 100 = INTOSC oscillator: I/O function on CLKIN pin
 - 011 = EXTRC oscillator: External RC circuit connected to CLKIN pin
 - 010 = HS oscillator: High-speed crystal/resonator connected between OSC1 and OSC2 pins
 - 001 = XT oscillator: Crystal/resonator connected between OSC1 and OSC2 pins
 - 000 = LP oscillator: Low-power crystal connected between OSC1 and OSC2 pins
- **Note 1:** Enabling Brown-out Reset does not automatically enable Power-up Timer.
 - 2: The entire data EEPROM will be erased when the code protection is turned off during an erase.
 - 3: The entire program memory will be erased when the code protection is turned off.



5: INTF is enabled to be set any time during the Q4-Q1 cycles.

EXAMPLE 11-5: WRITING TO FLASH PROGRAM MEMORY

; This write routine assumes the following:							
; 1. The 16 bytes of data are loaded, starting at the address in DATA_ADDR							
; 2. Each word of data to be written is made up of two adjacent bytes in DATA_ADDR,							
; stored in little endian format							
;	; 3. A valid starting address (the least significant bits = 000) is loaded in ADDRH:ADDRL						
;	4. AI	DDRH and ADD	RL are located i	n shared data memory 0x70 - 0x7F			
,	i						
DANKGEI FENDEL : Dank 2							
		MOVE	ADDRH, W	; Load initial address			
		MOVWF	EEADRH	;			
		MOVF	ADDRL,W	;			
		MOVWF	EEADRL	;			
		MOVLW	LOW DATA_ADDR	; Load initial data address			
		MOVWF	FSROL	;			
		MOVLW	HIGH DATA_ADDR	; Load initial data address			
		MOVWF	FSROH	;			
		BSF	EECON1,EEPGD	; Point to program memory			
		BCF	EECON1,CFGS	; Not configuration space			
		BSF	EECON1,WREN	; Enable writes			
		BSF	EECON1,LWLO	; Only Load Write Latches			
LС	UΡ	моуты	FCDUTT	: Load first data bute into lower			
		MOVIW	FEDATI.	:			
		MOVTW	FSR0++	, ; Load second data byte into upper			
		MOVWF	EEDATH	load second data byte into upper			
		MOVF	EEADRL,W	; Check if lower bits of address are '000'			
		XORLW	0x07	; Check if we're on the last of 8 addresses			
		ANDLW	0x07	;			
		BTFSC	STATUS, Z	; Exit if last of eight words,			
		GOTO	START_WRITE	;			
		MOVITW	5 5 b	· Start of required write genuerge:			
		MOVE	FECON2	: Write 55h			
		MOVIW	0AAh	:			
	nced	MOVWF	EECON2	; Write AAh			
	quii	BSF	EECON1,WR	; Set WR bit to begin write			
	Sec	NOP		; Any instructions here are ignored as processor			
	_ 0)			; halts to begin write sequence			
		NOP		; Processor will stop here and wait for write to complete.			
				; After write processor continues with 3rd instruction.			
		INCF	EEADRL, F	; Still loading latches Increment address			
		GOTO	LOOP	; Write next latches			
SI	ART_V	VRITE					
		BCF	EECON1,LWLO	; No more loading latches - Actually start Flash program			
				; memory write			
		MOVIW	55h	; Start of required write sequence:			
		MOVWF	EECON2	; Write 55h			
	ы В	MOVLW	0AAh	;			
	enc	MOVWF	EECON2	; Write AAh			
	eqเ €	BSF	EECON1,WR	; Set WR bit to begin write			
	ъ "	NOP		; Any instructions here are ignored as processor			
				; halts to begin write sequence			
		NOP		; Processor will stop here and wait for write complete.			
				: after write processor continues with and instruction			
		BCF	EECON1 . WREN	; Disable writes			
	BSF INTCON,GIE ; Enable interrupts						

FIGURE 23-4:	CARRIER LOW SYNCHRONIZATION (MDSHSYNC = 0, MDCLSYNC = 1)
Carrier High (CARH)	
Carrier Low (CARL)	
Modulator (MOD)	
MDCHSYNC = 0 MDCLSYNC = 1	
Active Carrier State	CARH X CARL CARH X CARL





25.5.7 GENERAL CALL ADDRESS SUPPORT

The addressing procedure for the I^2C bus is such that the first byte after the Start condition usually determines which device will be the slave addressed by the master device. The exception is the general call address which can address all devices. When this address is used, all devices should, in theory, respond with an acknowledge.

The general call address is a reserved address in the I²C protocol, defined as address 0x00. When the GCEN bit of the SSPxCON2 register is set, the slave module will automatically ACK the reception of this address regardless of the value stored in SSPxADD. After the slave clocks in an address of all zeros with the R/W bit clear, an interrupt is generated and slave

software can read SSPxBUF and respond. Figure 25-24 shows a general call reception sequence.

In 10-bit Address mode, the UA bit will not be set on the reception of the general call address. The slave will prepare to receive the second byte as data, just as it would in 7-bit mode.

If the AHEN bit of the SSPxCON3 register is set, just as with any other address reception, the slave hardware will stretch the clock after the eighth falling edge of SCLx. The slave must then set its ACKDT value and release the clock with communication progressing as it would normally.

FIGURE 25-24: SLAVE MODE GENERAL CALL ADDRESS SEQUENCE



25.5.8 SSPX MASK REGISTER

An SSPx Mask (SSPMSK) register (Register 25-5) is available in I²C Slave mode as a mask for the value held in the SSPxSR register during an address comparison operation. A zero ('0') bit in the SSPMSK register has the effect of making the corresponding bit of the received address a "don't care".

This register is reset to all '1's upon any Reset condition and, therefore, has no effect on standard SSPx operation until written with a mask value.

The SSPx Mask register is active during:

- 7-bit Address mode: address compare of A<7:1>.
- 10-bit Address mode: address compare of A<7:0> only. The SSPx mask has no effect during the reception of the first (high) byte of the address.



26.1.2.8 Asynchronous Reception Setup:

- Initialize the SPBRGH, SPBRGL register pair and the BRGH and BRG16 bits to achieve the desired baud rate (see Section 26.3 "EUSART Baud Rate Generator (BRG)").
- 2. Clear the ANSEL bit for the RX pin (if applicable).
- Enable the serial port by setting the SPEN bit. The SYNC bit must be clear for asynchronous operation.
- 4. If interrupts are desired, set the RCIE bit of the PIE1 register and the GIE and PEIE bits of the INTCON register.
- 5. If 9-bit reception is desired, set the RX9 bit.
- 6. Enable reception by setting the CREN bit.
- 7. The RCIF interrupt flag bit will be set when a character is transferred from the RSR to the receive buffer. An interrupt will be generated if the RCIE interrupt enable bit was also set.
- 8. Read the RCSTA register to get the error flags and, if 9-bit data reception is enabled, the ninth data bit.
- 9. Get the received eight Least Significant data bits from the receive buffer by reading the RCREG register.
- 10. If an overrun occurred, clear the OERR flag by clearing the CREN receiver enable bit.

26.1.2.9 9-bit Address Detection Mode Setup

This mode would typically be used in RS-485 systems. To set up an Asynchronous Reception with Address Detect Enable:

- Initialize the SPBRGH, SPBRGL register pair and the BRGH and BRG16 bits to achieve the desired baud rate (see Section 26.3 "EUSART Baud Rate Generator (BRG)").
- 2. Clear the ANSEL bit for the RX pin (if applicable).
- Enable the serial port by setting the SPEN bit. The SYNC bit must be clear for asynchronous operation.
- If interrupts are desired, set the RCIE bit of the PIE1 register and the GIE and PEIE bits of the INTCON register.
- 5. Enable 9-bit reception by setting the RX9 bit.
- 6. Enable address detection by setting the ADDEN bit.
- 7. Enable reception by setting the CREN bit.
- The RCIF interrupt flag bit will be set when a character with the ninth bit set is transferred from the RSR to the receive buffer. An interrupt will be generated if the RCIE interrupt enable bit was also set.
- 9. Read the RCSTA register to get the error flags. The ninth data bit will always be set.
- 10. Get the received eight Least Significant data bits from the receive buffer by reading the RCREG register. Software determines if this is the device's address.
- 11. If an overrun occurred, clear the OERR flag by clearing the CREN receiver enable bit.
- 12. If the device has been addressed, clear the ADDEN bit to allow all received data into the receive buffer and generate interrupts.



FIGURE 26-5: ASYNCHRONOUS RECEPTION

FIGURE 27-2: CAPACITIVE SENSING OSCILLATOR BLOCK DIAGRAM



RRF	Rotate Right f through Carry				
Syntax:	[<i>label</i>] RRF f,d				
Operands:	$0 \le f \le 127$ $d \in [0,1]$				
Operation:	See description below				
Status Affected:	С				
Description:	The contents of register 'f' are rotated one bit to the right through the Carry flag. If 'd' is '0', the result is placed in the W register. If 'd' is '1', the result is placed back in register 'f'.				



SUBLW	Subtract W from literal				
Syntax:	[label] St	JBLW k			
Operands:	$0 \leq k \leq 255$				
Operation:	$k - (W) \to (W$	/)			
Status Affected:	C, DC, Z				
Description:	The W register is subtracted (2's complement method) from the 8-bit literal 'k'. The result is placed in the W register.				
	C = 0 W > k				
	C = 1 W ≤ k				
	DC = 0 W<3:0> k<3:0>				

DC = 1

 $W<3:0> \le k<3:0>$

SLEEP	Enter Sleep mode			
Syntax:	[label] SLEEP			
Operands:	None			
Operation:	$\begin{array}{l} \text{O0h} \rightarrow \text{WDT}, \\ 0 \rightarrow \text{WDT prescaler}, \\ 1 \rightarrow \overline{\text{TO}}, \\ 0 \rightarrow \overline{\text{PD}} \end{array}$			
Status Affected:	TO, PD			
Description:	The power-down Status bit, $\overline{\text{PD}}$ is cleared. Time-out Status bit, $\overline{\text{TO}}$ is set. Watchdog Timer and its prescaler are cleared. The processor is put into Sleep mode with the oscillator stopped.			

SUBWF	Subtract W from f				
Syntax:	[label] SL	IBWF f,d			
Operands:	$\begin{array}{l} 0 \leq f \leq 127 \\ d \in [0,1] \end{array}$				
Operation:	(f) - (W) \rightarrow (d	estination)			
Status Affected:	C, DC, Z				
Description:	Subtract (2's complement method) W register from register 'f'. If 'd' is '0', the result is stored in the W register. If 'd' is '1', the result is stored back in register 'f.				
	W > f				
	C = 1	$W \leq f$			
	DC = 0	W<3:0> > f<3:0>			
	DC = 1	W<3:0> ≤ f<3:0>			

SUBWFB	Subtract W from f with Borrow			
Syntax:	SUBWFB f {,d}			
Operands:	$\begin{array}{l} 0 \leq f \leq 127 \\ d \in [0,1] \end{array}$			
Operation:	$(f) - (W) - (\overline{B}) \rightarrow dest$			
Status Affected:	C, DC, Z			
Description:	Subtract W and the BORROW flag (CARRY) from register 'f' (2's complement method). If 'd' is '0', the result is stored in W. If 'd' is '1', the result is stored back in register 'f'.			

30.4 DC Characteristics: PIC16(L)F1825/9-I/E

DC CHARACTERISTICS		Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial $-40^{\circ}C \le TA \le +125^{\circ}C$ for extended					
Param No.	Sym.	Characteristic	Min.	Тур†	Max.	Units	Conditions
	VIL	Input Low Voltage					
		I/O PORT:					
D030		with TTL buffer	—	_	0.8	V	$4.5V \leq V\text{DD} \leq 5.5V$
D030A			—	_	0.15 VDD	V	$1.8V \leq V\text{DD} \leq 4.5V$
D031		with Schmitt Trigger buffer	_		0.2 VDD	V	$2.0V \leq V\text{DD} \leq 5.5V$
		with I ² C™ levels		_	0.3 VDD	V	
		with SMBus levels		_	0.8	V	$2.7V \leq V\text{DD} \leq 5.5V$
D032		MCLR, OSC1 (RC mode) ⁽¹⁾	_	_	0.2 VDD	V	
D033		OSC1 (HS mode)	_		0.3 VDD	V	
	Viн	Input High Voltage	ļI				
		I/O ports:					
D040		with TTL buffer	2.0	_	_	V	$4.5V \le VDD \le 5.5V$
D040A			0.25 VDD +		_	V	$1.8V \le VDD \le 4.5V$
			0.8				
D041		with Schmitt Trigger buffer	0.8 VDD		—	V	$2.0V \leq V\text{DD} \leq 5.5V$
		with I ² C™ levels	0.7 VDD	_	—	V	
		with SMBus levels	2.1	_	—	V	$2.7V \leq V\text{DD} \leq 5.5V$
D042		MCLR	0.8 VDD	_	_	V	
D043A		OSC1 (HS mode)	0.7 VDD	_	_	V	
D043B		OSC1 (RC mode)	0.9 VDD	_	_	V	VDD > 2.0V (Note 1)
IIL Input Leakage Current ⁽²⁾							
D060		I/O ports	—	± 5	± 125	nA	$Vss \le VPIN \le VDD$, Pin at high-impedance at $85^{\circ}C$
		(2)		± 5	± 1000	nA	125°C
D061		MCLR ⁽³⁾		± 50	± 200	nA	$Vss \le VPIN \le VDD$ at $85^{\circ}C$
	IPUR	Weak Pull-up Current				1	
D070*			25	100	200		VDD = 3.3V, $VPIN = VSS$
	Vo	Output Low Valtage ⁽⁴⁾	25	140	300	μA	VDD = 5.0V, VPIN = VSS
D000	VOL						101 - 9mA $1/55 - 51/$
D080		I/O ports	_	_	0.6	V	IOL = 8 mA, $VDD = 5V$
				_	0.0	v	IOL = 1.8mA, VDD = 1.8V
	Voh	Output High Voltage ⁽⁴⁾					
D090		I/O ports				1	IOH = 3 5mA VDD = 5V
2000			VDD - 0.7	_	_	V	IOH = 3mA, $VDD = 3.3V$
							Іон = 1mA, Vdd = 1.8V
		Capacitive Loading Specs on	Output Pins				
D101*	COSC2	OSC2 pin	—	_	15	pF	In XT, HS and LP modes when external clock is used to drive OSC1
D101A*	Cio	All I/O pins	_	_	50	pF	
*	These		mat ta ata d		1		I

These parameters are characterized but not tested.

Data in "Typ" column is at 3.0V, 25°C unless otherwise stated. These parameters are for design guidance only and are † not tested.

Note 1: In RC oscillator configuration, the OSC1/CLKIN pin is a Schmitt Trigger input. It is not recommended to use an external clock in RC mode.

2: Negative current is defined as current sourced by the pin.

3: The leakage current on the MCLR pin is strongly dependent on the applied voltage level. The specified levels represent normal operating conditions. Higher leakage current may be measured at different input voltages.

4: Including OSC2 in CLKOUT mode.

DC CHARACTERISTICS			$\begin{array}{llllllllllllllllllllllllllllllllllll$				
Param No.	Sym.	Characteristic	Min.	Тур†	Max.	Units	Conditions
		Program Memory High Voltage Programming Specifications					
D110	VIHH	Voltage on MCLR/VPP/RA5 pin	8.0	_	9.0	V	(Note 3, 4)
D111	IDDVPP	Programming/Erase Current on VPP, High Voltage Programming	—	—	10	mA	
D112	VBE	VDD for Bulk Erase	2.7		VDDMAX	V	
D113	VPEW	VDD for Write or Row Erase	VDDMIN		VDDMAX	V	
D114	IPPPGM	Programming/Erase Current on VPP, Low Voltage Programming	—	1.0	—	mA	
D115	IDDPGM	Programming/Erase Current on VDD, High or Low Voltage Programming	—	5.0	—	mA	
		Data EEPROM Memory					
D116	ED	Byte Endurance	100K	—	—	E/W	-40°C to +85°C
D117	VDRW	VDD for Read/Write	VDDMIN	—	VDDMAX	V	
D118	TDEW	Erase/Write Cycle Time	—	4.0	5.0	ms	
D119	TRETD	Characteristic Retention	—	40	—	Year	Provided no other specifications are violated
D120	TREF	Number of Total Erase/Write Cycles before Refresh ⁽²⁾	1M	10M	—	E/W	-40°C to +85°C
		Program Flash Memory					
D121	Eр	Cell Endurance	10K	—	—	E/W	-40°C to +85°C (Note 1)
D122	VPRW	VDD for Read/Write	VDDMIN	—	VDDMAX	V	
D123	Tiw	Self-timed Write Cycle Time	—	2	2.5	ms	
D124	TRETD	Characteristic Retention	—	40	—	Year	Provided no other specifications are violated

30.5 Memory Programming Requirements

† Data in "Typ" column is at 3.0V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: Self-write and Block Erase.

2: Refer to Section 11.2 "Using the Data EEPROM" for a more detailed discussion on data EEPROM endurance.

3: Required only if single-supply programming is disabled.

4: The MPLAB ICD 2 does not support variable VPP output. Circuitry to limit the MPLAB ICD 2 VPP voltage must be placed between the MPLAB ICD 2 and target system when programming or debugging with the MPLAB ICD 2.

TABLE 30-5: **RESET, WATCHDOG TIMER, OSCILLATOR START-UP TIMER, POWER-UP TIMER** AND BROWN-OUT RESET PARAMETERS

Standard Operating Conditions (unless otherwise stated) Operating Temperature -40°C \leq TA \leq +125°C							
Param No.	Sym.	Characteristic	Min.	Тур†	Max.	Units	Conditions
30	TMCL	MCLR Pulse Width (low)	2	_	_	μs	
31	TWDTLP	Low-Power Watchdog Timer Time-out Period	12	16	20	ms	V _{DD} = 3.3V-5V, 1:16 Prescaler used
32	Tost	Oscillator Start-up Timer Period ⁽¹⁾	_	1024	_	Tosc	
33*	TPWRT	Power-up Timer Period, $\overline{PWRTE} = 0$	40	65	140	ms	
34*	Tioz	I/O high-impedance from MCLR Low or Watchdog Timer Reset	_	—	2.0	μS	
35	VBOR	Brown-out Reset Voltage ⁽²⁾	2.55 1.80	2.70 1.9	2.85 2.05	V V	BORV = 0 BORV = 1
36*	VHYST	Brown-out Reset Hysteresis	20	35	75	mV	-40°C to +85°C
37*	TBORDC	Brown-out Reset DC Response Time	1	3	35	μS	$VDD \leq VBOR$

These parameters are characterized but not tested.

Data in "Typ" column is at 3.0V, 25°C unless otherwise stated. These parameters are for design guidance t only and are not tested.

Note 1: By design, the Oscillator Start-up (OST) counts the first 1024 cycles, independent of frequency.

2: To ensure these voltage tolerances, VDD and VSS must be capacitively decoupled as close to the device as possible. 0.1 μ F and 0.01 μ F values in parallel are recommended.

FIGURE 30-10: TIMER0 AND TIMER1 EXTERNAL CLOCK TIMINGS



14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	N	S		
Dimension	Dimension Limits		NOM	MAX	
Contact Pitch	E	1.27 BSC			
Contact Pad Spacing	С		5.40		
Contact Pad Width	Х			0.60	
Contact Pad Length	Y			1.50	
Distance Between Pads	Gx	0.67			
Distance Between Pads	G	3.90			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A

20-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





l	Jnits	MILLIMETERS				
Dimension Limits		MIN	NOM	MAX		
Number of Pins	Ν	20				
Pitch	е	1.27 BSC				
Overall Height	А	-	2.65			
Molded Package Thickness	A2	2.05 -		-		
Standoff §	A1	0.10	-	0.30		
Overall Width	Е	10.30 BSC				
Molded Package Width	E1	7.50 BSC				
Overall Length	D	12.80 BSC				
Chamfer (Optional)	h	0.25	-	0.75		
Foot Length	L	0.40	-	1.27		
Footprint	L1	1.40 REF				
Lead Angle	Θ	0°	-	-		
Foot Angle	φ	0°	-	8°		
Lead Thickness	С	0.20	-	0.33		
Lead Width	b	0.31	-	0.51		
Mold Draft Angle Top	α	5°	-	15°		
Mold Draft Angle Bottom	β	5°	-	15°		

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-094C Sheet 2 of 2